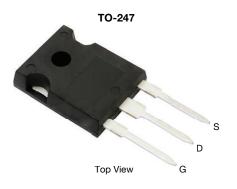
# SUG90090E

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**Vishay Siliconix** 

### N-Channel 200 V (D-S) 175 °C MOSFET



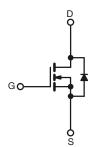
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	200				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = 10 V	0.0095				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = 7.5 V	0.0104				
Q <sub>g</sub> typ. (nC)	86				
I <sub>D</sub> (A)	100 <sup>d</sup>				
Configuration	Single				

#### **FEATURES**

- ThunderFET<sup>®</sup> power MOSFET
- Low R<sub>DS</sub> Q<sub>g</sub> figure-of-merit (FOM)
- Maximum 175 °C junction temperature
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **APPLICATIONS**

- Synchronous rectification
- Power supplies
- DC/AC inverter
- DC/DC converter
- · Solar micro inverter
- Motor drive switch



N-Channel MOSFET

# ORDERING INFORMATION Package TO-247 Lead (Pb)-free and halogen-free SUG90090E-GE3

ABSOLUTE MAXIMUM RATI	<b>NGS</b> (T <sub>A</sub> = 25 °C, u	Inless other	wise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	200	V	
Gate-source voltage		V <sub>GS</sub>	± 20	V	
Or attinuous during summert	T <sub>C</sub> = 25 °C		100 <sup>d</sup>		
Continuous drain current	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	77.6	Î	
Pulsed drain current (t = 100 µs)		I <sub>DM</sub>	300	А	
Continuous source-drain diode current		IS	100 <sup>d</sup>		
Single pulse avalanche current <sup>a</sup>		I <sub>AS</sub>	100	1	
Single pulse avalanche energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	500	mJ	
Martin and a state to the state of the state	T <sub>C</sub> = 25 °C		395 <sup>b</sup>	14/	
Maximum power dissipation $T_{C} = 125 \text{ °C}$		P <sub>D</sub>	132 <sup>b</sup>	W	
Operating junction and storage tempera	ture range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temp	erature) <sup>c</sup>		260		

THERMAL RESISTANCE RATING	iS			
PARAMETER		SYMBOL	MAXIMUM	UNIT
Maximum junction-to-ambient (PCB mount) <sup>c</sup>		R <sub>thJA</sub>	40	°C/W
Maximum junction-to-case (drain)	Steady state	R <sub>thJC</sub>	0.38	0/10

#### Notes

a. Duty cycle  $\leq$  1 %

b. See SOA curve for voltage derating

c. When mounted on 1" square PCB (FR4 material)

d. Package limited

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(Pb) RoHS

COMPLIANT

HALOGEN

FREE

# SUG90090E

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	200	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	2	-	4	V
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	-	-	250	nA
		$V_{DS} = 200 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	μA
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = 200 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	150	μΑ
		$V_{DS} = 200 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	5	mA
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	30	-	-	А
Durain acturate an atota registerias a	D	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	0.0079	0.0095	0
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 7.5 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	-	0.0083	0.0104	Ω
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	-	54	-	S
Dynamic <sup>b</sup>					•	
Input capacitance	Ciss		-	5220	-	
Output capacitance	C <sub>oss</sub>	$V_{DS}$ = 100 V, $V_{GS}$ = 0 V, f = 1 MHz	-	495	-	pF
Reverse transfer capacitance	C <sub>rss</sub>		-	51	-	1
Total gate charge	Qg		-	86	129	
Gate-source charge	Q <sub>gs</sub>	$V_{DS}$ = 100 V, $V_{GS}$ =10 V, $I_{D}$ = 20 A	-	23	-	nC
Gate-drain charge	Q <sub>gd</sub>		-	22.7	-	1
Gate resistance	Rg	f = 1 MHz	0.6	3.2	14.4	Ω
Turn-on delay time	t <sub>d(on)</sub>		-	18	27	
Rise time	t <sub>r</sub>	V <sub>DD</sub> = 100 V, R <sub>L</sub> = 6.7 Ω, I <sub>D</sub> ≅ 15 A,	-	44	66	
Turn-off delay time	t <sub>d(off)</sub>	$V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$	-	60	90	ns
Fall time	t <sub>f</sub>		-	40	60	
Drain-Source Body Diode Characteristi	cs				•	
Pulse diode forward current (t = 100 µs)	I <sub>SM</sub>		-	-	100	А
Body diode voltage	V <sub>SD</sub>	I <sub>F</sub> = 15 A, V <sub>GS</sub> = 0 V	-	0.85	1.5	V
Body diode reverse recovery time	t <sub>rr</sub>		-	146	220	ns
Body diode reverse recovery charge	Q <sub>rr</sub>		-	0.91	1.37	μC
Reverse recovery fall time	t <sub>a</sub>	I <sub>F</sub> = 15 A, di/dt = 100 A/μs	-	115	-	
Reverse recovery rise time	t <sub>b</sub>		-	31	-	ns
Body diode peak reverse recovery charge	I <sub>RM(REC)</sub>		-	12	18	Α

#### Notes

a. Pulse test; pulse width  $\leq 300~\mu\text{s},~\text{duty~cycle} \leq 2~\%$ 

b. Guaranteed by design, not subject to production testing

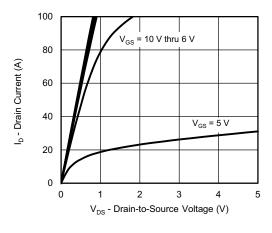
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

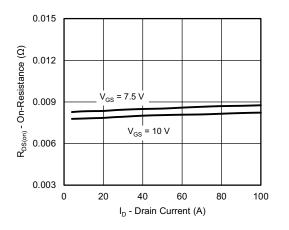
2



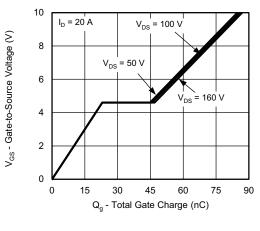
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



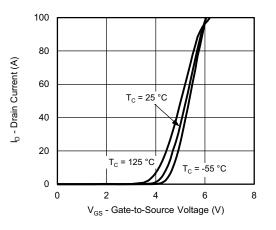
**Output Characteristics** 



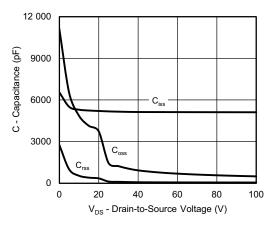
**On-Resistance vs. Drain Current and Gate Voltage** 



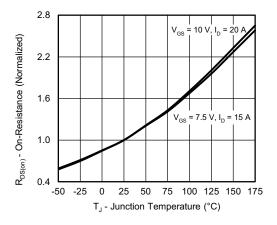
Gate Charge



**Transfer Characteristics** 



Capacitance



**On-Resistance vs. Junction Temperature** 

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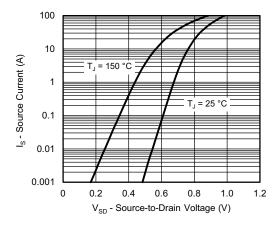
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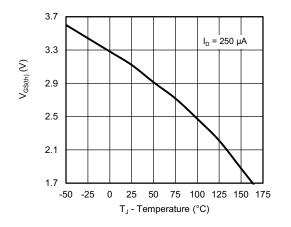
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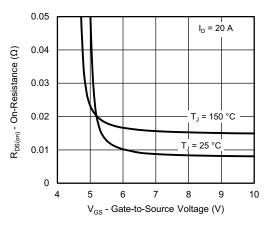
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



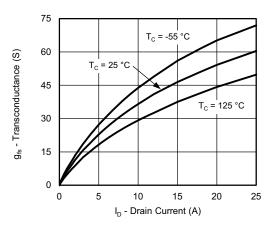
Source-Drain Diode Forward Voltage



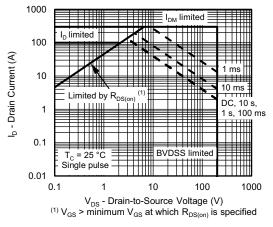
**Threshold Voltage** 



**On-Resistance vs. Gate-to-Source Voltage** 



Transconductance



Safe Operating Area, Junction-to-Ambient

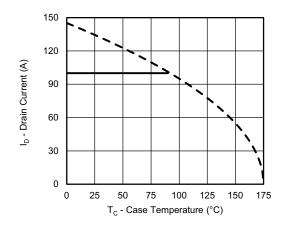
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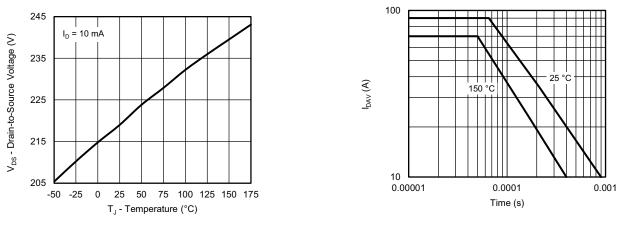
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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)







Drain Source Breakdown vs. Junction Temperature

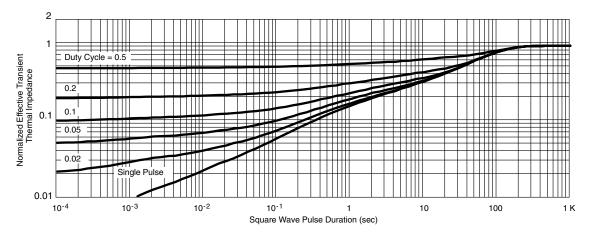
IDAV vs. Time

#### Note

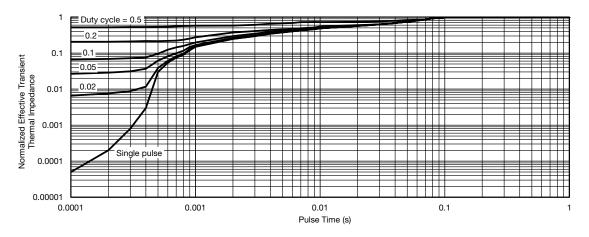
a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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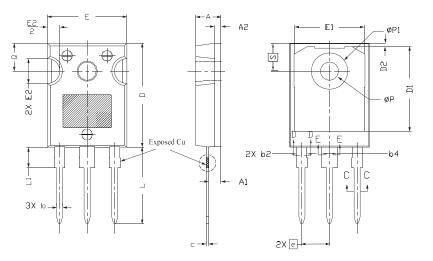
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**TO-247AC (High Voltage)** 

#### VERSION 1: FACILITY CODE = 9





(	

	М	ILLIMETERS		
DIM.	MIN.	NOM.	MAX.	NOTES
А	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.17	1.27	1.37	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
С	0.40	0.50	0.60	6
c1	0.40	0.50	0.56	
D	20.40	20.55	20.70	4

		MILLIMETERS	S	
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
E	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
е		5.46 BSC		
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
ØР	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S		5.51 BSC		

#### Notes

- <sup>(1)</sup> Package reference: JEDEC<sup>®</sup> TO247, variation AC
- (2) All dimensions are in mm
- <sup>(3)</sup> Slot required, notch may be rounded
- <sup>(4)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- <sup>(5)</sup> Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



#### VERSION 2: FACILITY CODE = Y



	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

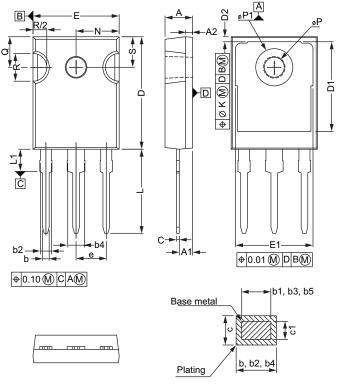
#### Notes

- <sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994
- <sup>(2)</sup> Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- <sup>(4)</sup> Thermal pad contour optional with dimensions D1 and E1
- <sup>(5)</sup> Lead finish uncontrolled in L1
- <sup>(6)</sup> Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- <sup>(7)</sup> Outline conforms to JEDEC outline TO-247 with exception of dimension c

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#### VERSION 3: FACILITY CODE = N



MILLIMETERS		MILLIMETERS			
DIM.	MIN.	MAX.	DIM.	MIN.	MAX
А	4.65	5.31	D2	0.51	1.35
A1	2.21	2.59	E	15.29	15.87
A2	1.17	1.37	E1	13.46	-
b	0.99	1.40	e	5.46	BSC
b1	0.99	1.35	k	0.:	254
b2	1.65	2.39	L	14.20	16.10
b3	1.65	2.34	L1	3.71	4.29
b4	2.59	3.43	N	7.62	BSC
b5	2.59	3.38	Р	3.56	3.66
С	0.38	0.89	P1	-	7.39
c1	0.38	0.84	Q	5.31	5.69
D	19.71	20.70	R	4.52	5.49
D1	13.08	-	S	5.51	BSC

Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

<sup>(2)</sup> Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

<sup>(4)</sup> Thermal pad contour optional with dimensions D1 and E1

<sup>(5)</sup> Lead finish uncontrolled in L1

<sup>(6)</sup> Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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